

Amendment to the Abstract:

Please replace the abstract with the rewritten abstract provided on a separate sheet attached hereto.

Attachment: Replacement Sheet for Abstract

ABSTRACT

A method forms fin structures for a semiconductor device. The method includes forming a first fin structure including a dielectric material and including a first side surface and a second side surface; forming a second fin structure adjacent the first side surface of the first fin structure; and forming a third fin structure adjacent the second side surface of the first fin structure. The second fin structure and the third fin structure are formed of a different material than the first fin structure.